

#### HN7G02FE

Unit: mm

TOSHIBA Multichip Discrete Device

HN7G02FE

WWW.

#### Power Management Switch Applications, Inverter Circuit Applications, Driver Circuit Applications and Interface Circuit Applications

Q1 (transistor): RN2110 equivalent

Q2 (MOSFET): SSM3K03FE equivalent

#### Q1 (Transistor) Absolute Maximum Ratings (Ta = 25°C)

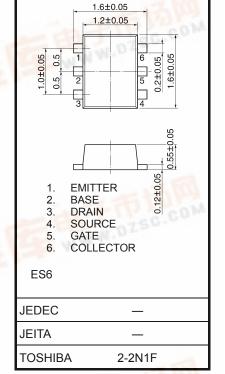
Characteristic	Symbol	Rating	Unit		
Collector-base voltage	V <sub>CBO</sub>	-50	V		
Collector-emitter voltage	V <sub>CEO</sub>	-50	V		
Emitter-base voltage	V <sub>EBO</sub>	-5	V		
Collector current	Ι <sub>C</sub>	-100	mA		

#### Q2 (MOSFET) Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V <sub>DS</sub>	20	V
Gate-source voltage	V <sub>GSS</sub>	10	V
DC drain current	Ι <sub>D</sub>	50	mA

#### Q1, Q2 Common Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Power dissipation	P (Note 1)	100	mW
Junction temperature	U.BTISC.	150	°C
Storage temperature range	T <sub>stg</sub>	-55~150	°C



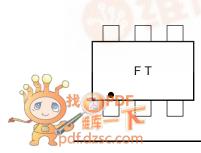
Weight:0.003g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

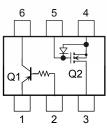
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

#### Marking



#### Equivalent Circuit (top view)



### Q1 (Transistor) Electrical Characteristics (Ta = 25°C)

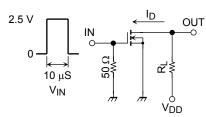
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB}=-50~V,~I_{E}=0$	_	_	-100	nA
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = -5 \text{ V}, \text{ I}_{C} = 0$	_	_	-100	nA
DC current gain	h <sub>FE</sub>	$V_{CE} = -5 \text{ V}, \text{ I}_{C} = -1 \text{ mA}$	120	_	400	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	$I_C = -5$ mA, $I_B = -0.25$ mA	_	-0.1	-0.3	V
Input resistor	R1	_	3.29	4.7	6.11	kΩ

### Q2 (MOSFET) Electrical Characteristics (Ta = 25°C)

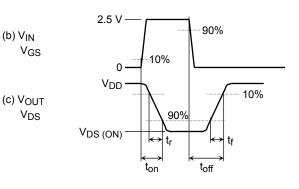
Characteristics Symbol Test Condition		Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 0$	_	_	1	μA
Drain-source breal	kdown voltage	V (BR) DSS	$I_D = 100 \ \mu A, \ V_{GS} = 0$	20	_	—	V
Drain cutoff curren	t	I <sub>DSS</sub>	$V_{DS} = 20 V, V_{GS} = 0$	_	_	1	μA
Gate threshold vol	tage	V <sub>th</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 0.1 \text{ mA}$	0.7	_	1.3	V
Forward transfer a	dmittance	Y <sub>fs</sub>	$V_{DS} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}$	25	50	_	mS
Drain-source ON-r	resistance	R <sub>DS (ON)</sub>	$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$	_	4	12	Ω
Input capacitance		C <sub>iss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	11.0	_	pF
Reverse transfer c	apacitance	C <sub>rss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	3.3	_	pF
Output capacitance		C <sub>oss</sub>	$V_{DS} = 3 V, V_{GS} = 0, f = 1 MHz$	_	9.3		pF
Switching time	Turn-on time	t <sub>on</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 2.5 \text{ V}$	_	0.16		0
	Turn-off time	t <sub>off</sub>	$V_{DD} = 3 \text{ V}, \text{ I}_{D} = 10 \text{ mA}, \text{ V}_{GS} = 0 2.5 \text{ V}$	_	0.19		μS

### Switching Time Test Circuit

(a) Switching time test circuit

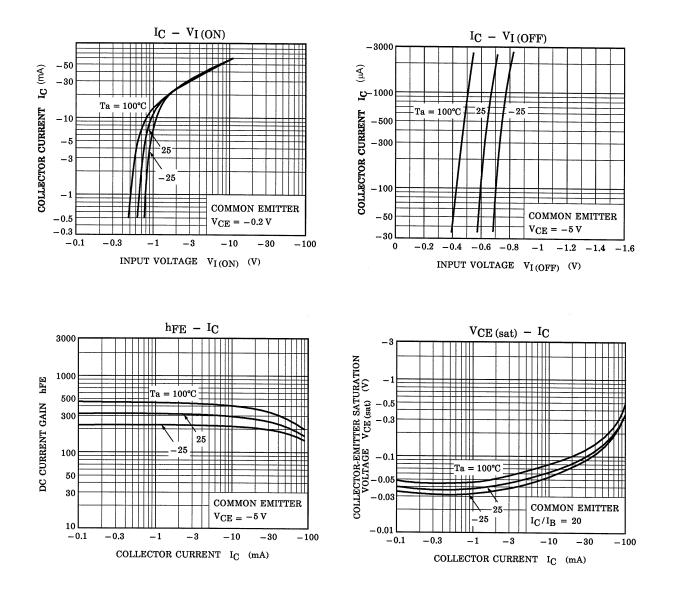


$$\begin{split} &V_{DD}=3 \ V\\ &D.U. \leq 1\%\\ &V_{IN}: t_r, t_f < 5 \ ns\\ &(Z_{out}=50 \ \Omega)\\ &Common \ source\\ &Ta=25^\circ C \end{split}$$

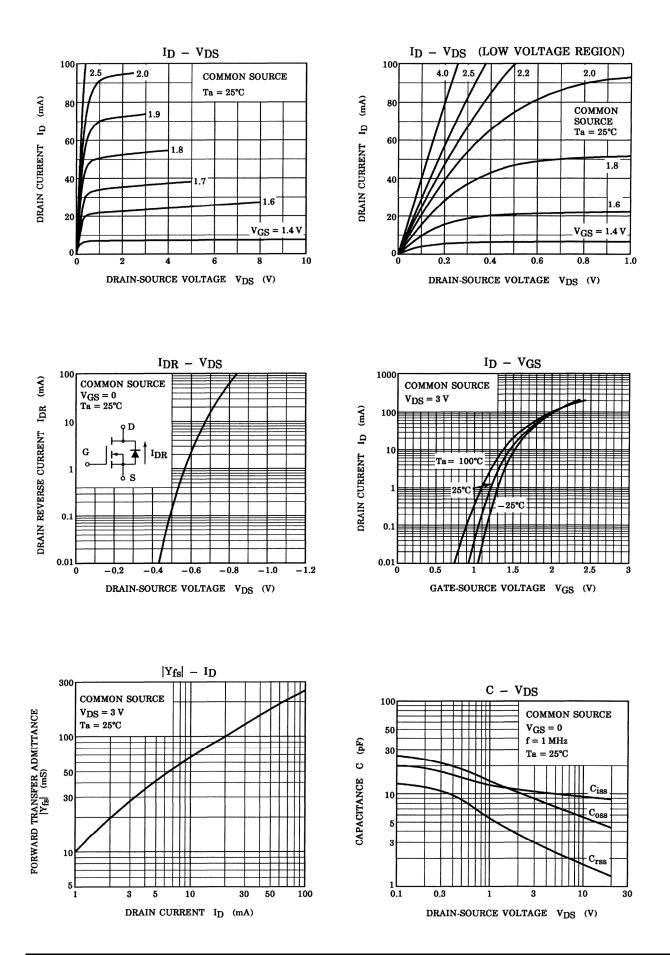


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### Q1 (Transistor)

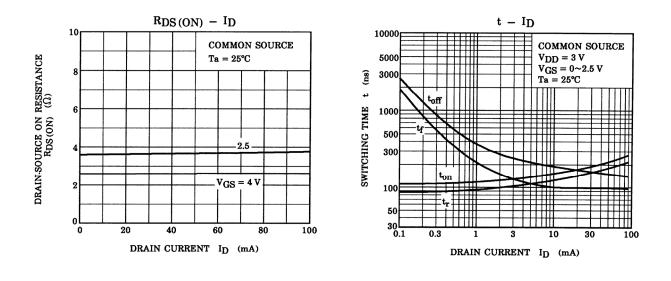


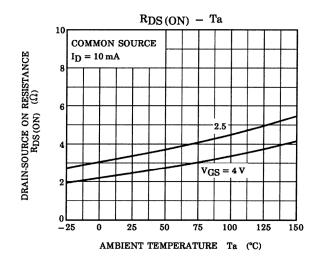
#### Q2 (MOSFET)



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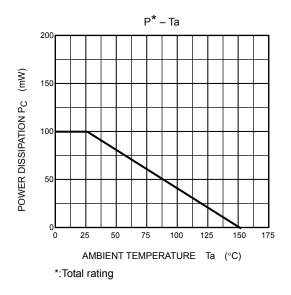
### Q2 (MOSFET)





## HN7G02FE

## Q1, Q2 Common



## TOSHIBA

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Handbook" etc.

20070701-EN GENERAL

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